

NPN MEDIUM POWER TRANSISTORS IN SOT89

Features

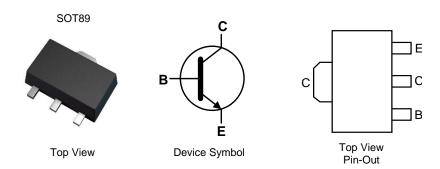
- BV_{CEO} > 45V, 60V & 80V
- I_c = 1A Continuous Collector Current
- I_{CM} = 2A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < 500mV @ 0.5A
- Gain Groups 10 and 16
- Epitaxial Planar Die Construction
- Complementary PNP Types: BCX51, 52, and 53
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Leads.
 Solderable per MIL-STD-202 Method 208 (e3)
- Weight: 0.055 grams (Approximate)

Applications

- Medium Power Switching or Amplification Applications
- AF Driver and Output Stages



Ordering Information (Notes 4 & 5)

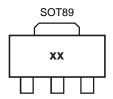
| Product | Compliance | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel | | |
|-------------|------------|--|--------------------|-----------------|-------------------|--|--|
| BCX54TA | AEC-Q101 | BA | 7 | 12 | 1,000 | | |
| BCX5410TA | AEC-Q101 | ВС | 7 | 12 | 1,000 | | |
| BCX5416TA | AEC-Q101 | BD | 7 | 12 | 1,000 | | |
| BCX5416-13R | AEC-Q101 | BD | 13 | 12 | 4,000 | | |
| BCX55TA | AEC-Q101 | BE | 7 | 12 | 1,000 | | |
| BCX5510TA | AEC-Q101 | BG | 7 | 12 | 1,000 | | |
| BCX5516TA | AEC-Q101 | BM | 7 | 12 | 1,000 | | |
| BCX56TA | AEC-Q101 | ВН | 7 | 12 | 1,000 | | |
| BCX5610TA | AEC-Q101 | BK | 7 | 12 | 1,000 | | |
| BCX5616TA | AEC-Q101 | BL | 7 | 12 | 1,000 | | |
| BCX5616TC | AEC-Q101 | BL | 13 | 12 | 4,000 | | |
| BCX5410TC | AEC-Q101 | ВС | 13 | 12 | 4,000 | | |
| BCX5416TC | AEC-Q101 | BD | 13 | 12 | 4,000 | | |
| BCX54TC | AEC-Q101 | BA | 13 | 12 | 4,000 | | |
| BCX5510TC | AEC-Q101 | BG | 13 | 12 | 4,000 | | |
| BCX5516TC | AEC-Q101 | BM | 13 | 12 | 4,000 | | |
| BCX55TC | AEC-Q101 | BE | 13 | 12 | 4,000 | | |
| BCX5610TC | AEC-Q101 | BK | 13 | 12 | 4,000 | | |
| BCX56TC | AEC-Q101 | ВН | 13 | 12 | 4,000 | | |
| BCX5616QTA | Automotive | Refer to http://diodes.com/datasheets/BCX5616Q.pdf | | | | | |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



xx = Product Type Marking Code, as follows:

BCX55 = BE BCX56 = BH BCX54 = BABCX5510 = BG BCX5610 = BK BCX5410 = BCBCX5416 = BD BCX5516 = BMBCX5616 = BL

Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | BCX54 | BCX55 | BCX56 | Unit |
|------------------------------|------------------|-------|-------|-------|-------|
| Collector-Base Voltage | V _{CBO} | 45 | 60 | 100 | V |
| Collector-Emitter Voltage | V _{CEO} | 45 | 60 | 80 | V |
| Emitter-Base Voltage | V _{EBO} | 6 | | | V |
| Continuous Collector Current | Ic | 1 | | | Δ |
| Peak Pulse Collector Current | I _{CM} | 2 | | | A |
| Continuous Base Current | I _B | 100 | | A | |
| Peak Pulse Base Current | I _{BM} | 200 | | | mA mA |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|---|-----------------|-----------------|------|------|--|
| | (Note 6) | | 1 | | |
| Power Dissipation | (Note 7) | P_D | 1.5 | W | |
| | (Note 8) | | 2.0 | | |
| | (Note 6) | | 125 | | |
| Thermal Resistance, Junction to Ambient Air | (Note 7) | $R_{\theta JA}$ | 83 | °C/W | |
| | (Note 8) | | 60 | | |
| Thermal Resistance, Junction to Lead | (Note 9) | $R_{	heta JL}$ | 13 | °C/W | |
| Operating and Storage Temperature Range | $T_{J,}T_{STG}$ | -65 to +150 | °C | | |

ESD Ratings (Note 10)

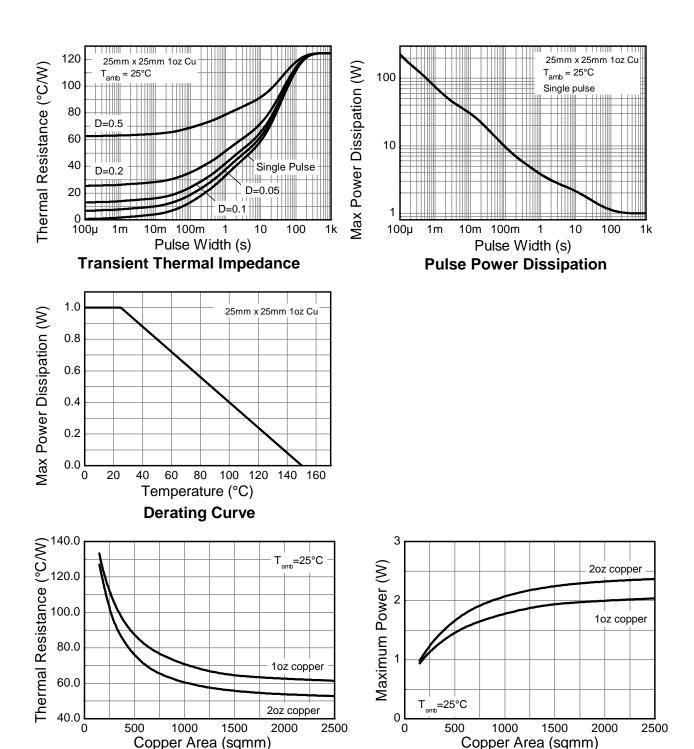
| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V | 3A |
| Electrostatic Discharge - Machine Model | ESD MM | 400 | V | С |

Notes:

- 6. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper. 8. Same as Note 6, except the device is mounted on 50mm x 50mm 1oz copper.
- 9. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information



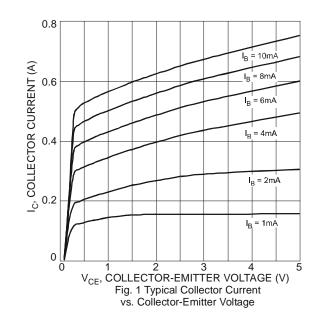


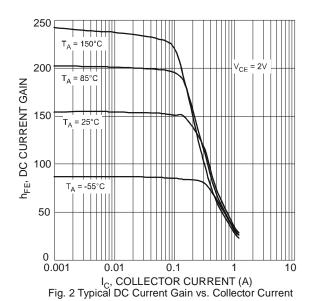
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Min | Тур | Max | Unit | Test Condition |
|--|-------------------------|----------------------|----------------------|-------------|-----------------|------|--|
| Collector-Base Breakdown Voltage | BCX54 BCX55 BCX56 | BV _{CBO} | 45 60 100 | _ | _ | V | I _C = 100μA |
| Collector-Emitter Breakdown Voltage (Note 11) | BCX54 BCX55 BCX56 | BV _{CEO} | 45 60 80 | _ | _ | V | I _C = 10mA |
| Emitter-Base Breakdown Voltage | | BV_{EBO} | 6 | _ | _ | V | $I_E = 100\mu A$ |
| Collector Cut-Off Current | | Ісво | _ | _ | 0.1 20 | μΑ | V _{CB} = 30V V _{CB} = 30V, T _A = +150°C |
| Emitter Cut-Off Current | | I _{EBO} | _ | _ | 20 | nA | V _{EB} = 5V |
| Static Forward Current Transfer Ratio (Note 11) | All versions | h _{FE} | 25 40 25 63 | _ _ _ | 250 — 160 | _ | I _C = 5mA, V _{CE} = 2V I _C = 150mA, V _{CE} = 2V I _C = 500mA, V _{CE} = 2V I _C = 150mA, V _{CE} = 2V |
| | 16 gain grp | | 100 | _ | 250 | | $I_C = 150 \text{mA}, V_{CE} = 2 \text{V}$ |
| Collector-Emitter Saturation Voltage (Note 11) | | V _{CE(sat)} | _ | _ | 0.5 | V | I _C = 500mA, I _B = 50mA |
| Base-Emitter Turn-On Voltage (Note 11) | | $V_{BE(on)}$ | _ | _ | 1.0 | V | I _C = 500mA, V _{CE} = 2V |
| Transition Frequency | | fτ | 150 | _ | _ | MHz | I _C = 50mA, V _{CE} = 10V f = 100MHz |
| Output Capacitance | | Cobo | _ | _ | 25 | pF | V _{CB} = 10V, f = 1MHz |

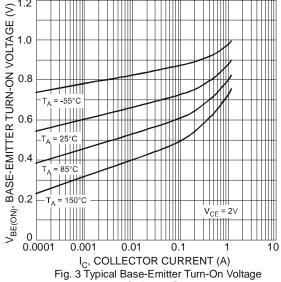
Note:

11. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

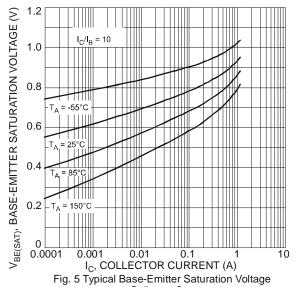


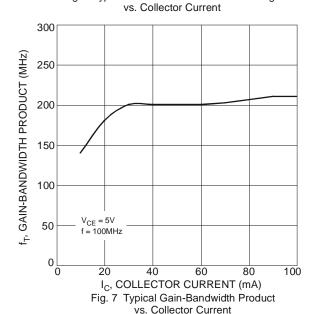






vs. Collector Current





0.4 $I_{\rm C}/I_{\rm B} = 10$ V_{CE(SAT)}, COLLECTOR-EMITTER SATURATION VOLTAGE (V) 0.3 0.2 0.1 T_A = 25°C = -55°C 0 .001 0.01 0.1 1 I_C, COLLECTOR CURRENT (A) 0.001 0.0001 10

Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

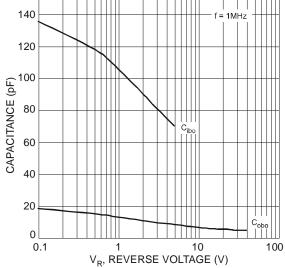
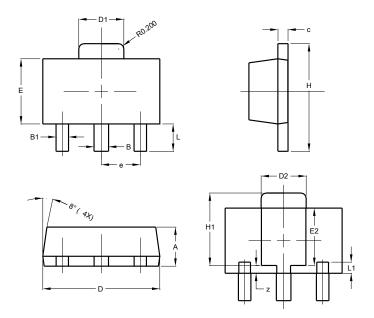


Fig. 6 Typical Capacitance Characteristics



Package Outline Dimensions

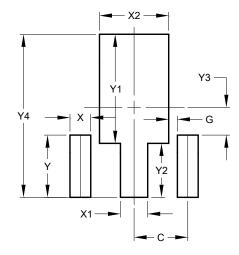
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



| SOT89 | | | | | |
|----------------------|-------|-------|-------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 1.40 | 1.60 | 1.50 | | |
| В | 0.50 | 0.62 | 0.56 | | |
| B1 | 0.42 | 0.54 | 0.48 | | |
| С | 0.35 | 0.43 | 0.38 | | |
| D | 4.40 | 4.60 | 4.50 | | |
| D1 | 1.62 | 1.83 | 1.733 | | |
| D2 | 1.61 | 1.81 | 1.71 | | |
| Е | 2.40 | 2.60 | 2.50 | | |
| E2 | 2.05 | 2.35 | 2.20 | | |
| е | - | - | 1.50 | | |
| Н | 3.95 | 4.25 | 4.10 | | |
| H1 | 2.63 | 2.93 | 2.78 | | |
| L | 0.90 | 1.20 | 1.05 | | |
| L1 | 0.327 | 0.527 | 0.427 | | |
| Z | 0.20 | 0.40 | 0.30 | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) | | |
|------------|------------------|--|--|
| С | 1.500 | | |
| | | | |
| G | 0.244 | | |
| Х | 0.580 | | |
| X1 | 0.760 | | |
| X2 | 1.933 | | |
| Υ | 1.730 | | |
| Y1 | 3.030 | | |
| Y2 | 1.500 | | |
| Y3 | 0.770 | | |
| Y4 | 4.530 | | |



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